NVD5862N

Power MOSFET

60 V, 5.7 mΩ, 98 A, Single N−Channel

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

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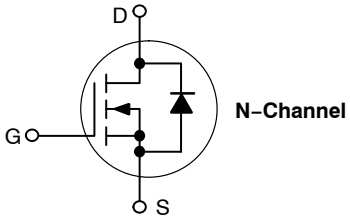
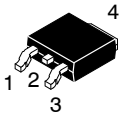
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
60 V	5.7 mΩ @ 10 V	98 A





DPAK
CASE 369C
(Surface Mount)
STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	60	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	T_C = 25°C	I_D	98	A
		T_C = 100°C		69	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	115	W
		T_C = 100°C		58	
Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 2)	Steady State	T_A = 25°C	I_D	18	A
		T_A = 100°C		13	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)		T_A = 25°C	P_D	4.1	W
		T_A = 100°C		2.0	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	367	A
Current Limited by Package (Note 3)	T_A = 25°C		$I_{Dmaxpkg}$	60	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	96	A
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{DD} = 50 V, V_{GS} = 10 V, $I_{L(pk)}$ = 37 A, L = 0.3 mH, R_G = 25 Ω)			E_{AS}	205	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

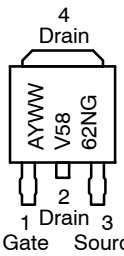
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Drain)	$R_{\theta JC}$	1.3	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	37	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
3. Continuous DC current rating. Maximum current for pulses as long as 1 second are higher but are dependent on pulse duration and duty cycle.

MARKING DIAGRAMS & PIN ASSIGNMENT



A = Assembly Location*
Y = Year
WW = Work Week
V5862N = Device Code
G = Pb−Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				47		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			1.0	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−9.7		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 48 A			4.4	5.7	mΩ
Forward Transconductance	gFS	V_{DS} = 15 V, I_D = 10 A			18		S
CHARGES, CAPACITANCES AND GATE RESISTANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			5050	6000	pF
Output Capacitance	C_{oss}				500	600	
Reverse Transfer Capacitance	C_{rss}				300	420	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 48 V, I_D = 48 A			82		nC
Threshold Gate Charge	$Q_{G(TH)}$				5.2		
Gate−to−Source Charge	Q_{GS}				24		
Gate−to−Drain Charge	Q_{GD}				27		
Gate Resistance	R_G				0.6		Ω
SWITCHING CHARACTERISTICS (Note 5)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 48 V, I_D = 48 A, R_G = 2.5 Ω			18		ns
Rise Time	t_r				70		
Turn−Off Delay Time	$t_{d(off)}$				35		
Fall Time	t_f				60		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 48 A	T_J = 25°C		0.9	1.2	V
			T_J = 100°C		0.75		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 48 A			38		ns
Charge Time	ta				20		
Discharge Time	tb				18		
Reverse Recovery Charge	Q_{RR}				40		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Order Number	Package	Shipping†
NVD5862NT4G	DPAK (Pb−Free)	2500 / Tape & Reel
NVD5862NT4G−VF01	DPAK (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

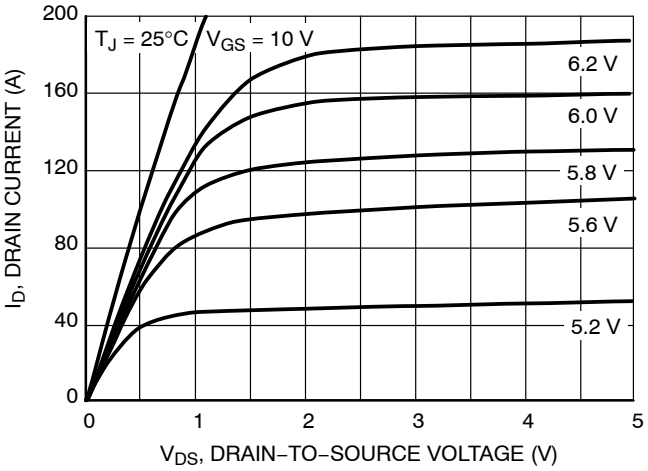


Figure 1. On−Region Characteristics

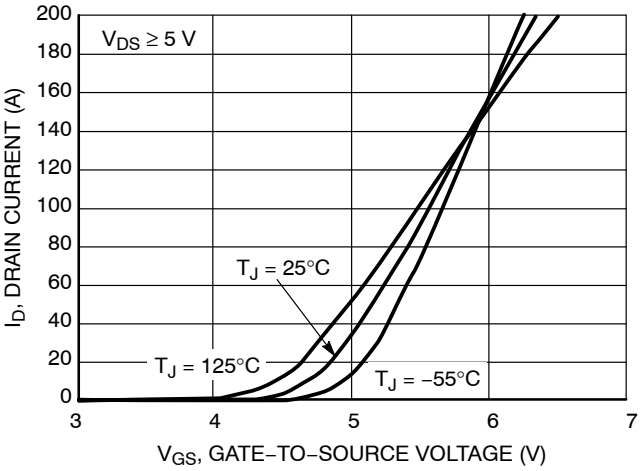


Figure 2. Transfer Characteristics

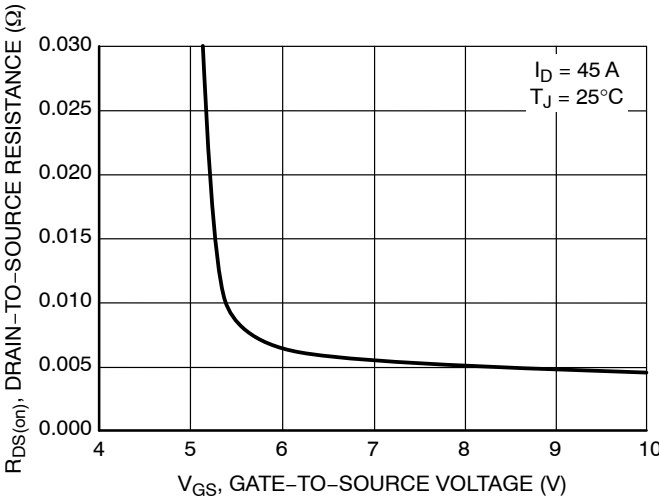


Figure 3. On−Resistance vs. Gate Voltage

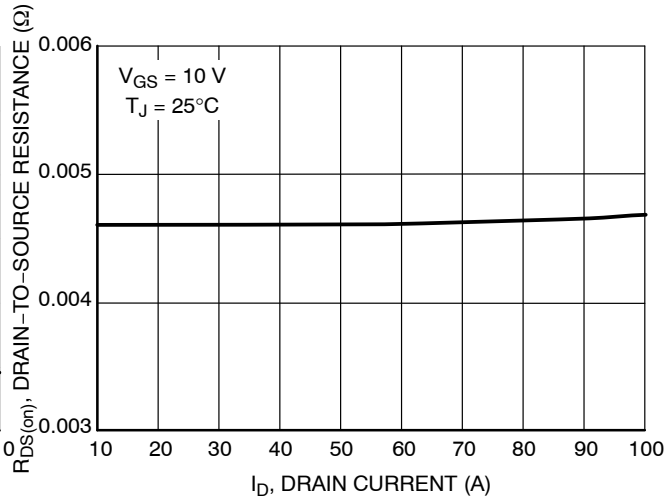


Figure 4. On−Resistance vs. Drain Current

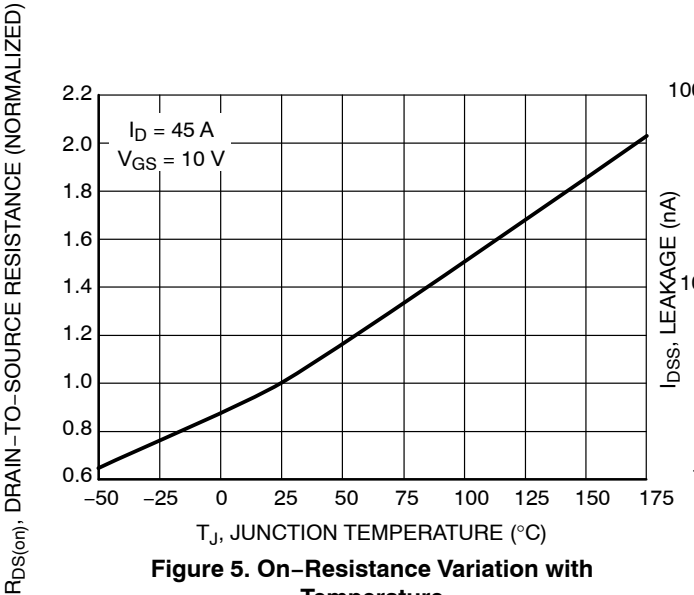


Figure 5. On−Resistance Variation with Temperature

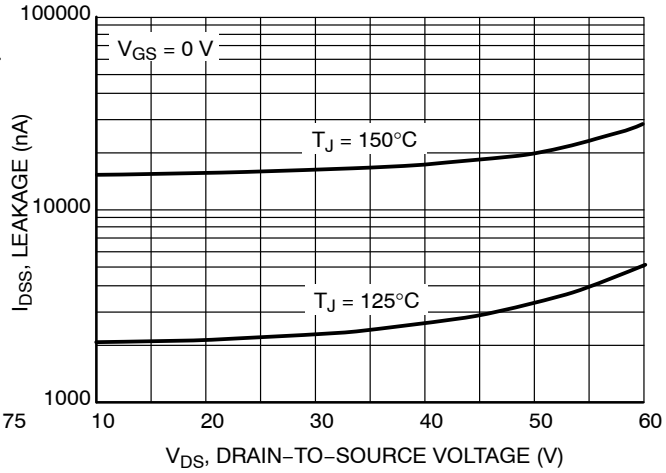


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

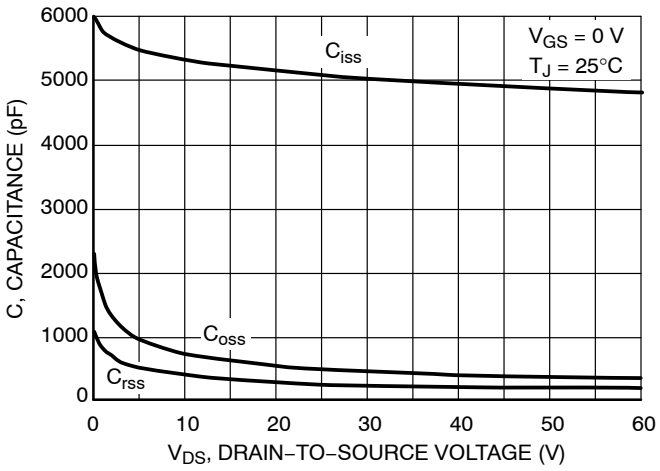


Figure 7. Capacitance Variation

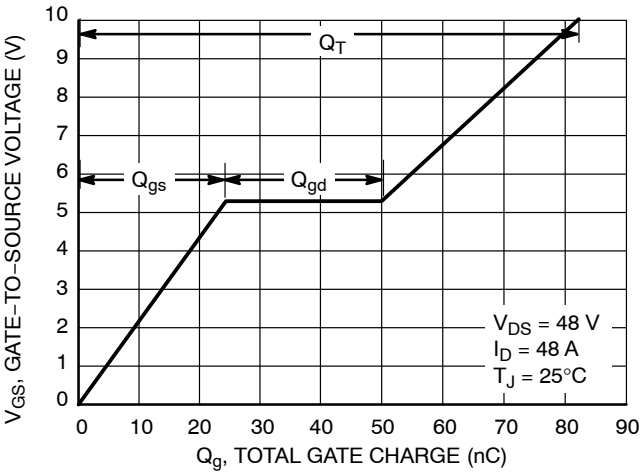


Figure 8. Gate−to−Source vs. Total Charge

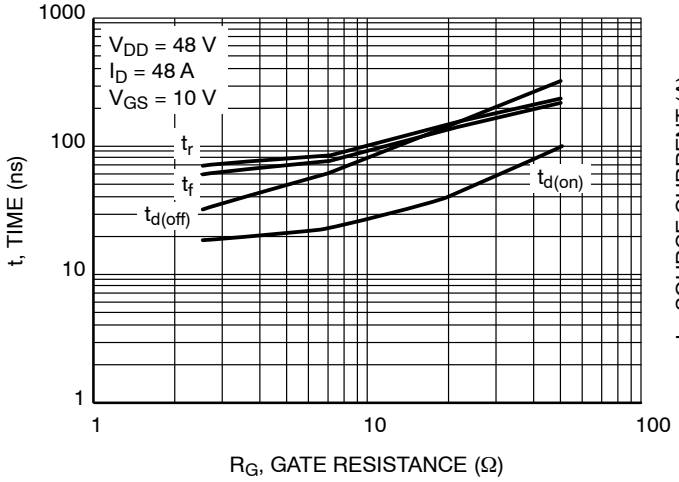


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

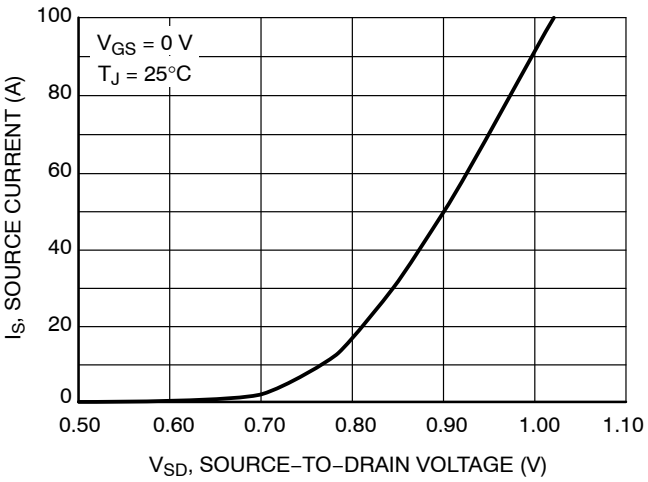


Figure 10. Diode Forward Voltage vs. Current

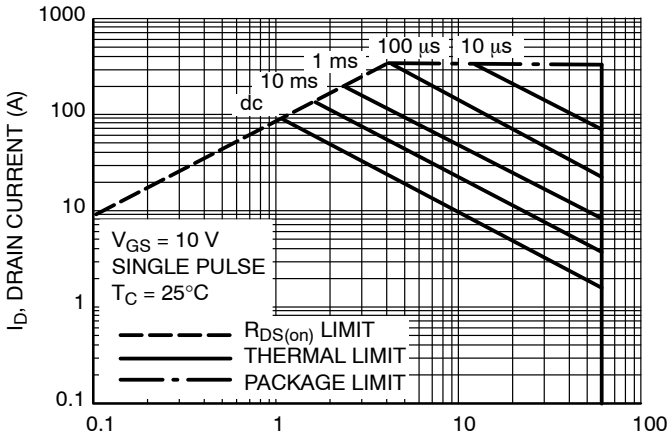


Figure 11. Maximum Rated Forward Biased Safe Operating Area

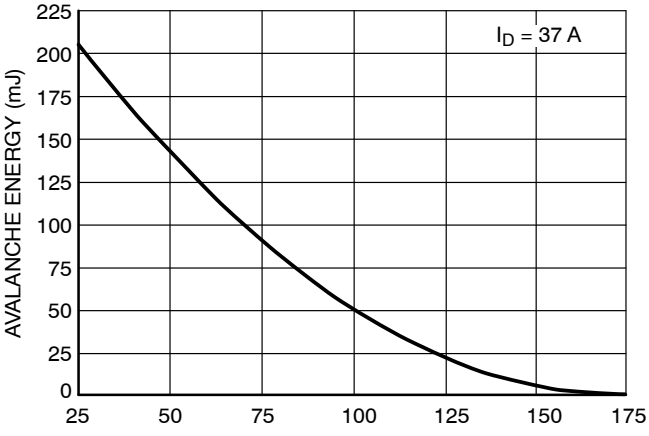


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

TYPICAL CHARACTERISTICS

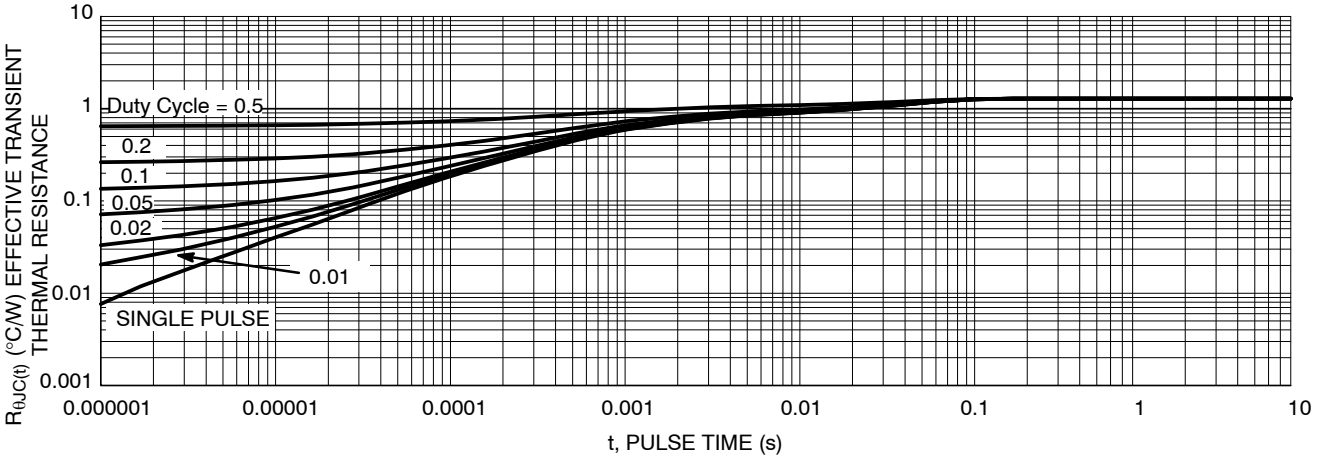
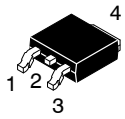


Figure 13. Thermal Response

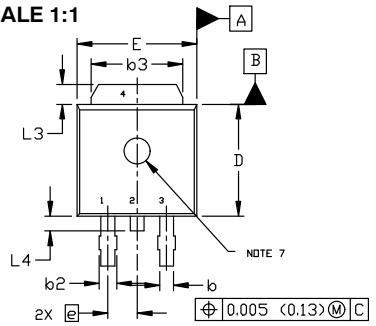
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



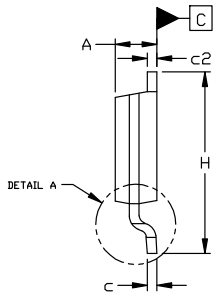
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

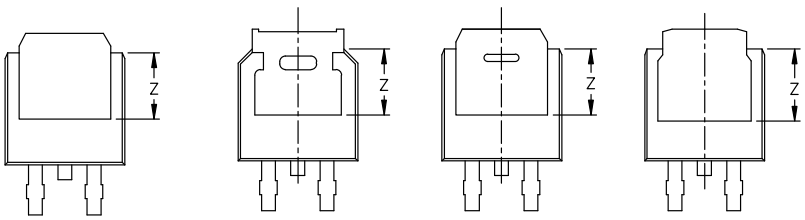


SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

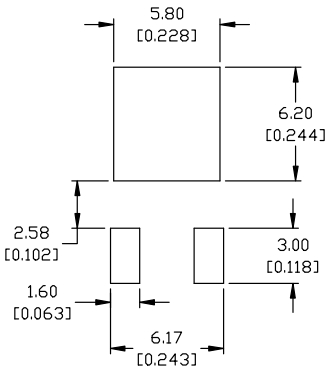
DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---



BOTTOM VIEW

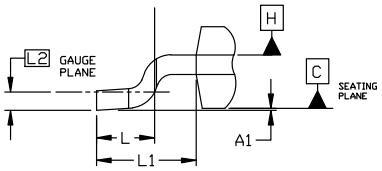
BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



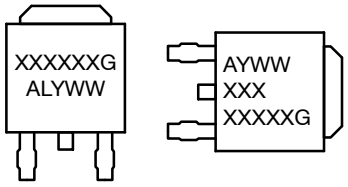
RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



DETAIL A
ROTATED 90° CW

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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DESCRIPTION:	**DPAK (SINGLE GAUGE)**	**PAGE 1 OF 1**

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